

Supporting Information

Eco-friendly, solution-processed In-W-O thin films and their applications in low-voltage, high-performance transistors

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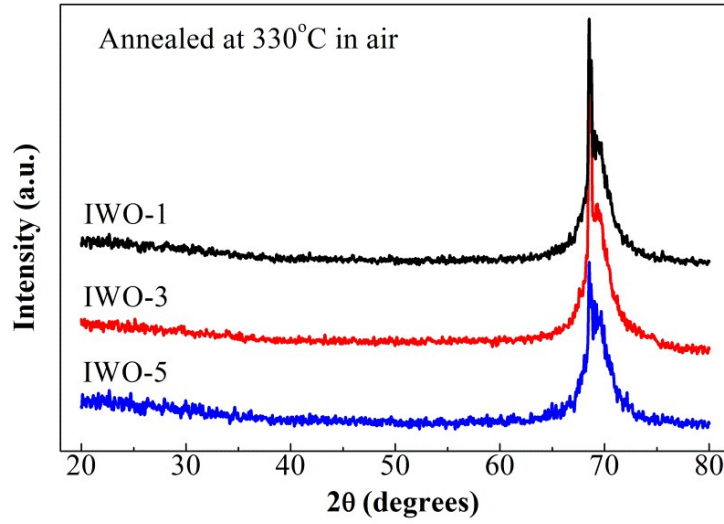


Fig. S1 XRD patterns of IWO thin films as a function of W concentration annealed at 330 °C.

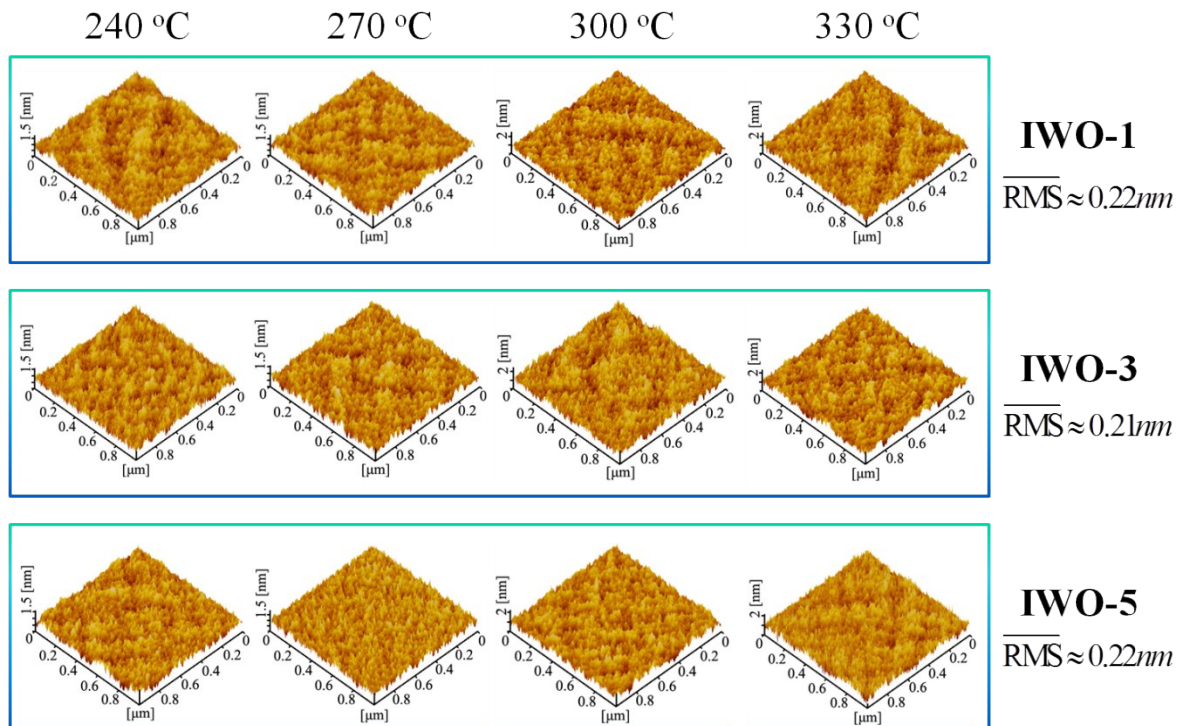


Fig. S2 AFM images of IWO thin films prepared at various annealing conditions.

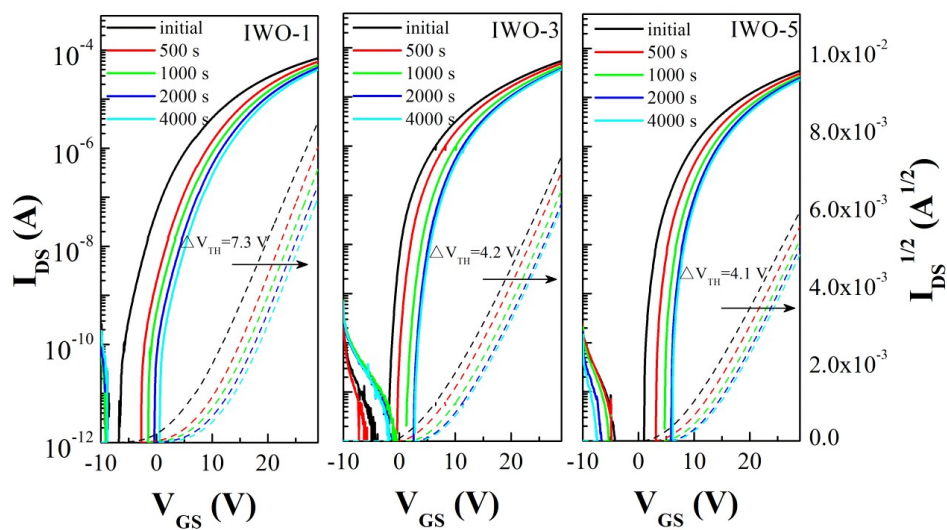


Fig. S3 Variation in the transfer characteristics of TFTs with IWO-1, IWO-3, and IWO-5 channel layers under PBS test for the duration of 4000 s.

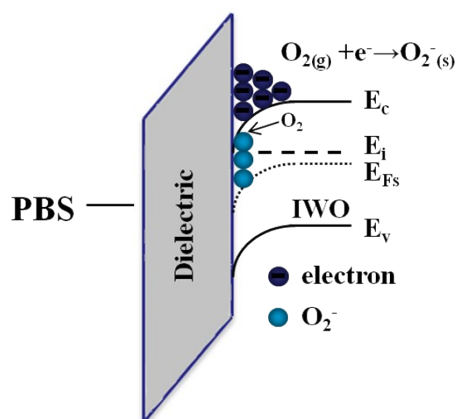


Fig. S4 Energy band diagrams of the IWO TFT under PBS test in air.